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PN - JP2002313076 A 20021025

TI - FERROELECTRIC MEMORY DEVICE

AB - **PROBLEM TO BE SOLVED:** To realize a ferroelectric memory device by which occurrence of imprint in a ferroelectric memory cell can be detected by using a simpler and smaller scale circuit than a Sawyer-Tower circuit.  
**SOLUTION:** The occurrence of imprint can surely be detected by using a simpler and smaller scale circuit than the Sawyer-Tower circuit by providing a preserved temperature measuring circuit 3 for judging whether the imprint is caused in the ferroelectric memory cell of a memory cell section 2 or not based on data of accumulated stress caused by high temperature preservation of the ferroelectric memory device itself. The size of the ferroelectric memory device can be made small.

I - G11C11/22

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